N-Channel JFET

J109, MMBFJ108

Features

- This Device is Designed for Digital Switching Applications where Very Low On Resistance is Mandatory
- Sourced from Process 58
- These are Pb-Free Devices

MAXIMUM RATINGS (T _A = 25°C unless otherwise specified) (Notes 1, 2)

Symbol	ymbol Parameter		Unit
V _{DG}	V _{DG} Drain-Gate Voltage		V
V _{GS}	V _{GS} Gate-Source Voltage		V
I _{GF}	I _{GF} Forward Gate Current		mA
T _J , T _{STG} Operating and Storage Junction Temperature Range		–55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

		Ma	ax	
Symbol	Parameter	J109 (Note 3)	MMBFJ108 (Note 4)	Unit
PD	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	125	-	°C/W
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient	200	357	°C/W

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

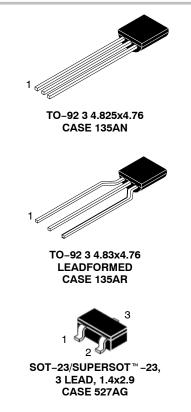
3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

 Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm².



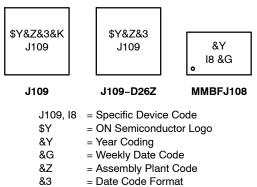
ON Semiconductor®

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1. Drain, 2. Source, 3. Gate

MARKING DIAGRAM



&K = Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conc	Test Condition		Max	Unit
DFF CHARACTERISTICS						
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_{G} = -10 \ \mu A, V_{DS} = 0$		-25	_	V
I _{GSS}	Gate Reverse Current	$V_{GS} = -15 \text{ V}, \text{ V}_{DS} = 0$	$V_{GS} = -15 \text{ V}, V_{DS} = 0$		-3.0	nA
		$V_{GS} = -15 \text{ V}, \text{ V}_{DS} = 0, \text{ T}_{A}$	V_{GS} = -15 V, V_{DS} = 0, T_A = 100°C		-200	
V _{GS} (off)	Gate-Source Cut-Off Voltage	V _{DS} = 15 V, I _D = 10 nA	MMBFJ108	-3.0	-10.0	V
			J109	-2.0	-6.0	

ON CHARACTERISTICS

I _{DSS}	Zero-Gate Voltage Drain Current (Note 5)	$V_{DS} = 15 V, V_{GS} = 0$	MMBFJ108	80	-	mA
			J109	40	-	
r _{DS} (on)	Drain-Source On Resistance	$V_{DS}{\leq}0.1$ V, $V_{GS}{=}0$	MMBFJ108	-	8.0	Ω
			J109	-	12	

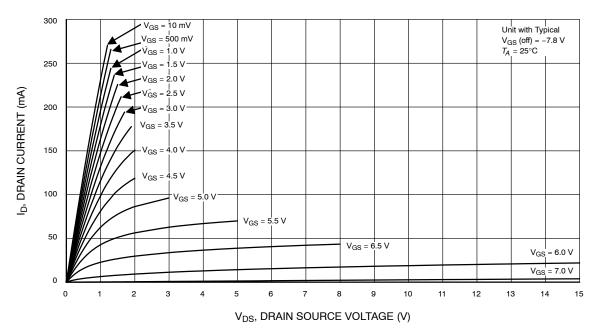
SMALL SIGNAL CHARACTERISTICS

C _{dg} (on) C _{sg} (off)	Drain-Gate & Source-Gate On Capacitance	V_{DS} = 0, V_{GS} = 0, f = 1.0 MHz	_	85	pF
C _{dg} (off)	Drain-Gate Off Capacitance	V_{DS} = 0, V_{GS} = -10 V, f = 1.0 MHz	-	15	pF
C _{sg} (off)	Source-Gate Off Capacitance	$V_{DS} = 0, V_{GS} = -10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$	-	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

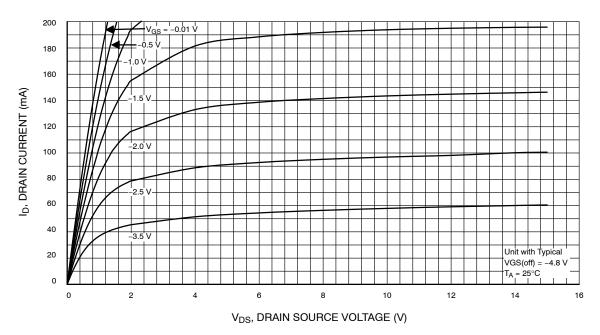
5. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2%.

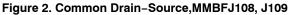
TYPICAL PERFORMANCE CHARACTERISTICS





TYPICAL PERFORMANCE CHARACTERISTICS (continued)





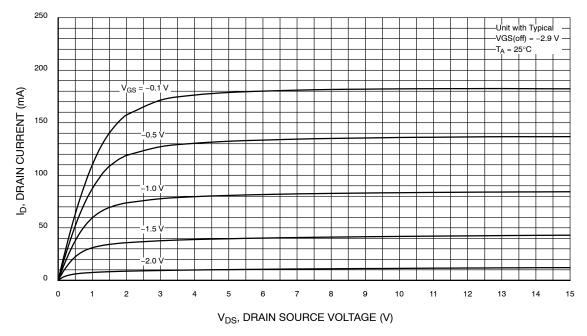
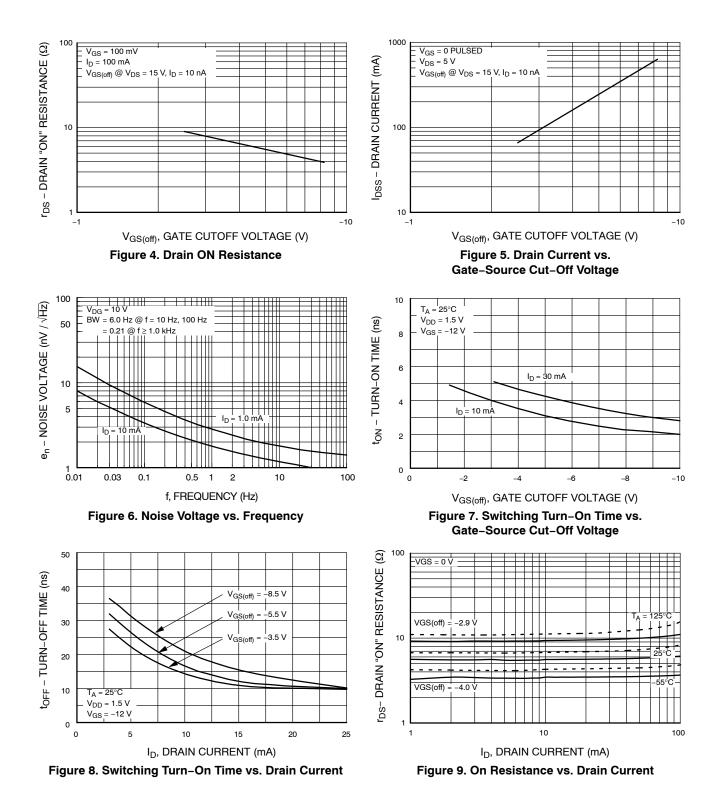


Figure 3. Common Drain–Source, J109

TYPICAL PERFORMANCE CHARACTERISTICS (continued)



TYPICAL PERFORMANCE CHARACTERISTICS (continued)

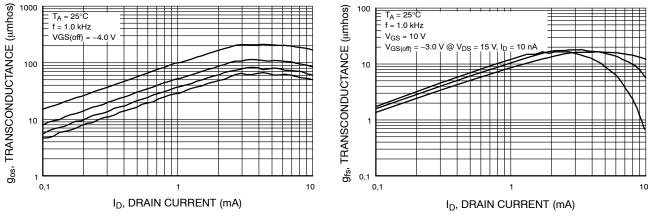


Figure 10. Output Conductance vs. Drain Current

Figure 11. Output Conductance vs. Drain Current

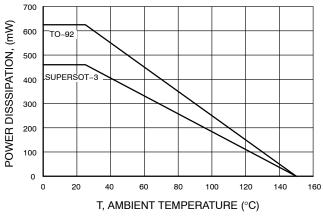


Figure 12. Power Dissipation vs. Ambient Temperature

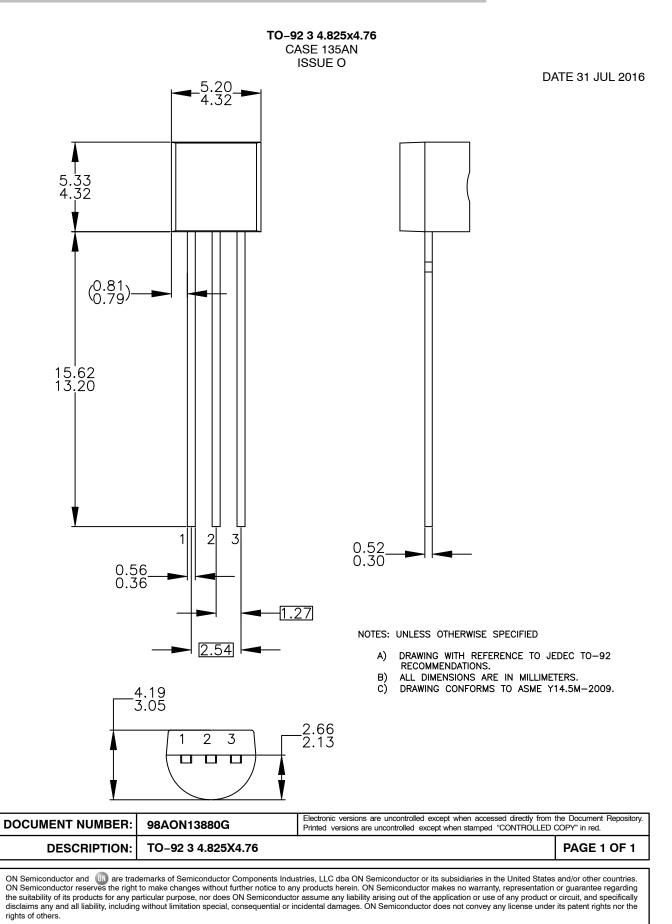
ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
J109	J109	TO-92 3L (Pb-Free)	10000 Units / Bulk
J109-D26Z	J109	TO-92 3L (Pb-Free)	2000 / Tape & Reel
MMBFJ108	18	SSOT 3L (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

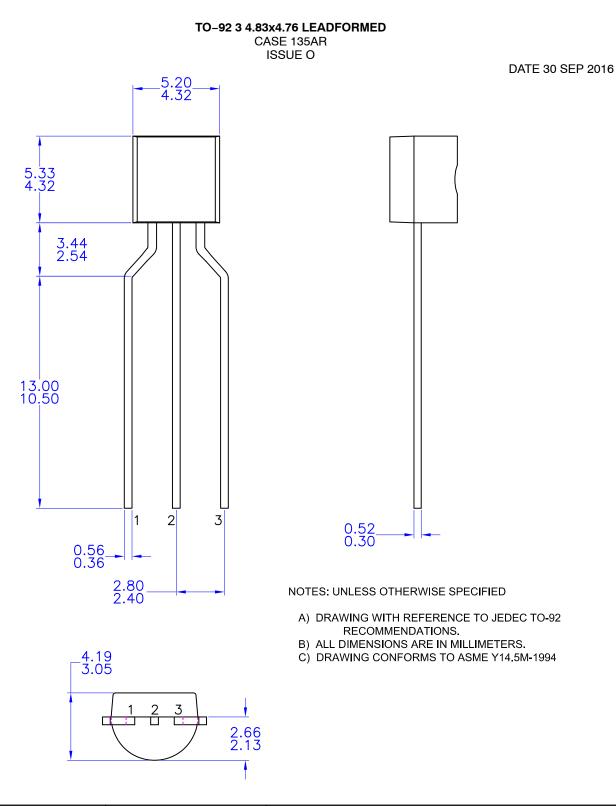
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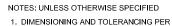
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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

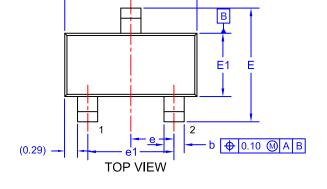


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DATE 09 DEC 2019

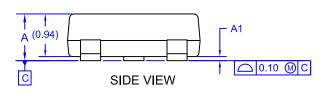


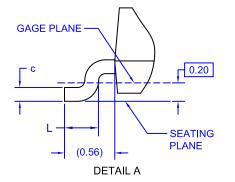
ASME Y14.5M, 2009. ALL DIMENSIONS ARE IN MILLIMETERS 2.

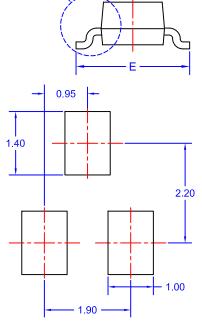


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2. 3.	DIMENS	IONS ARE EXCLUSIVE OF BURRS, LASH AND TIE BAR EXTRUSIONS.					
	DIM	MIN.	NOM.	MAX.			
	А	0.85	0.95	1.12			
	A1	0.00	0.05	0.10			
	b	0.370	0.435	0.508			
	с	0.085	0.150	0.180			
	D	2.80	2.92	3.04			
	Е	2.31	2.51	2.71			
	E1	1.20	1.40	1.52			
	е	0.95 BSC 1.90 BSC					
	e1						
	L	0.33	0.38	0.43			







SEE DETAIL A

LAND PATTERN RECOMMENDATION* *FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may

GENERIC **MARKING DIAGRAM***

XXXM=

XXX = Specific Device Code = Month Code Μ

= Pb-Free Package

or may not be present. Some products may (Note: Microdot may be in either location) not follow the Generic Marking.

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